

N-Channel 25-V (D-S) MOSFET

PRODUCT SUMMARY

V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ)
25	0.0027 at V _{GS} = 10 V	36	49 nC
	0.0032 at V _{GS} = 4.5 V	29	

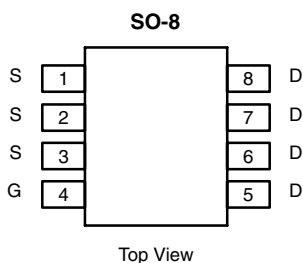
FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g Tested

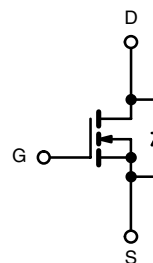


APPLICATIONS

- Synchronous Buck - Low Side
 - Notebook
 - Server
 - Workstation
- Synchronous Rectifier - POL



Ordering Information: Si4630DY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	25	V
Gate-Source Voltage	V _{GS}	± 16	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	A
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Pulsed Drain Current	I _{DM}	70	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	
Single Pulse Avalanche Current	I _{AS}	30	
Avalanche Energy	E _{AS}	45	mJ
Maximum Power Dissipation	P _D	T _C = 25 °C	W
		T _C = 70 °C	
		T _A = 25 °C	
		T _A = 70 °C	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	29	35	°C/W
Maximum Junction-to-Foot (Drain)	R _{thJF}	13	16	

Notes:

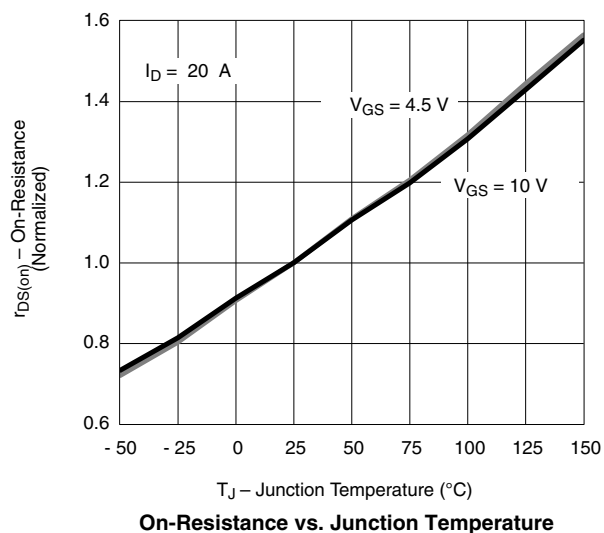
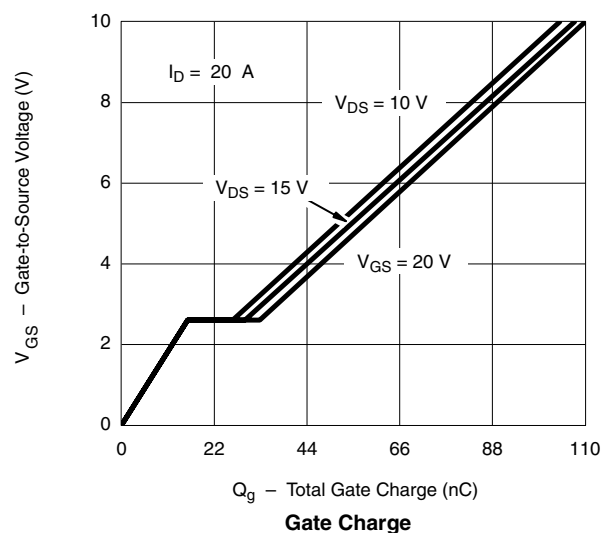
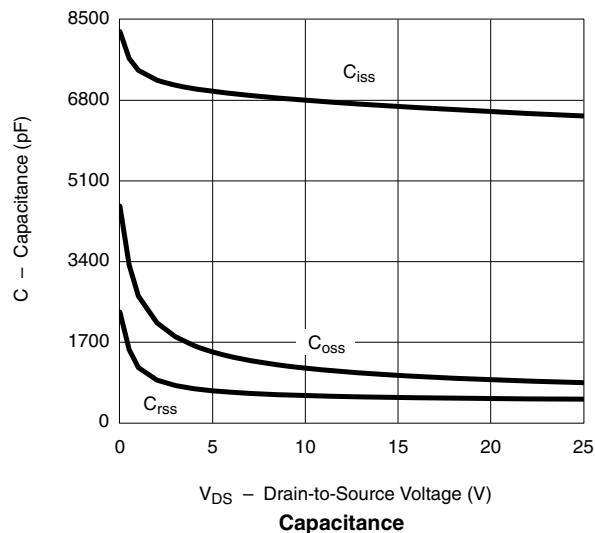
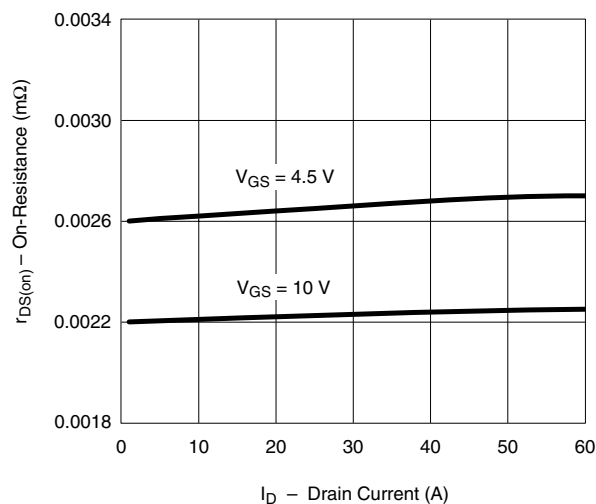
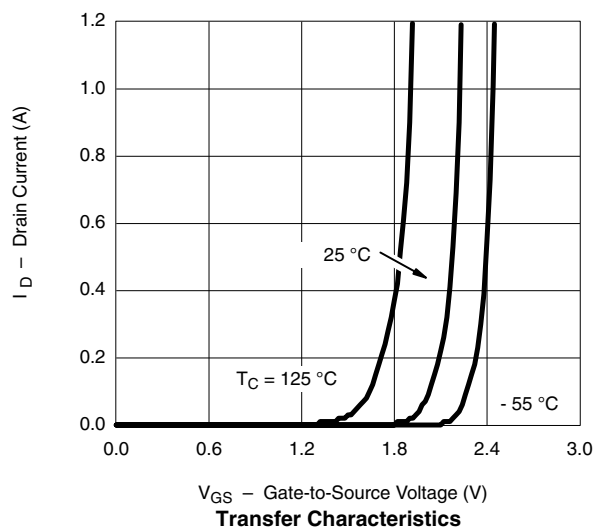
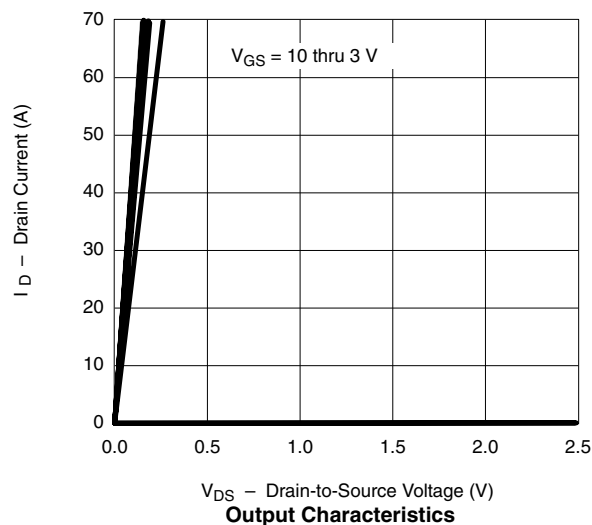
- Based on T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 sec.
- Maximum under Steady State conditions is 80 °C/W.

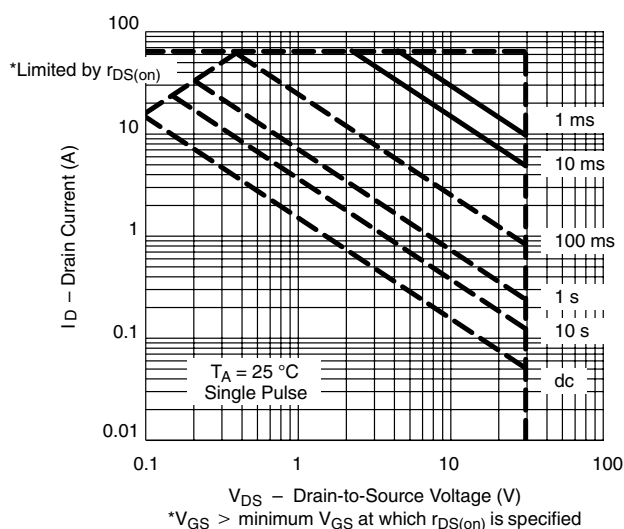
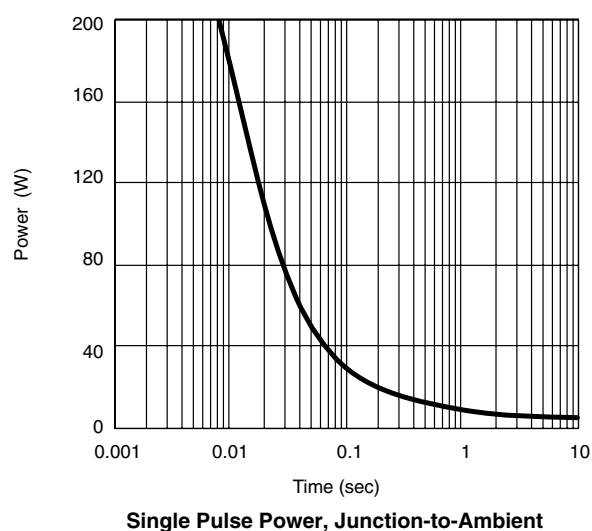
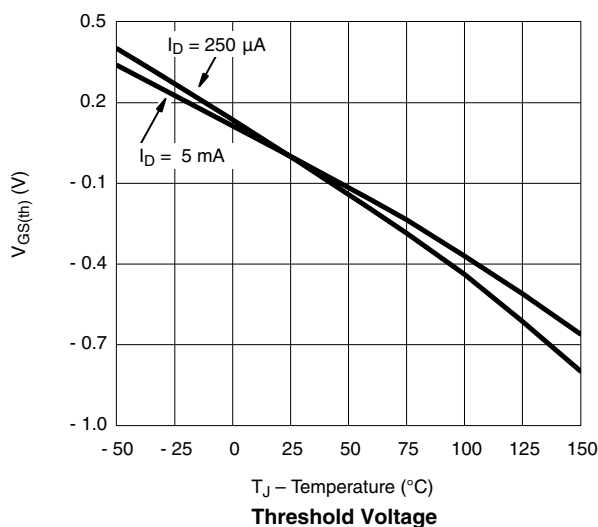
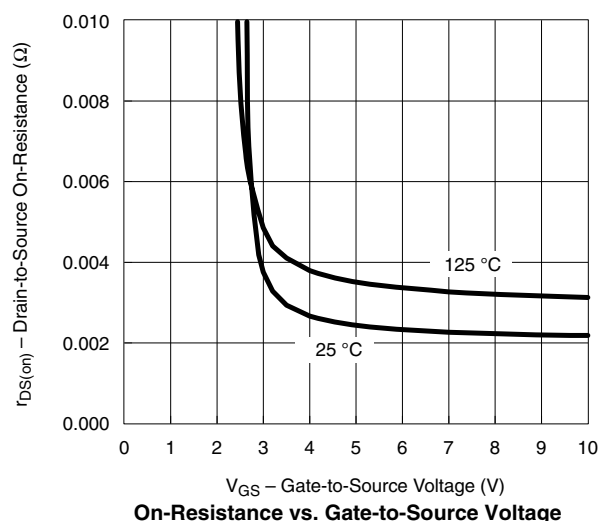
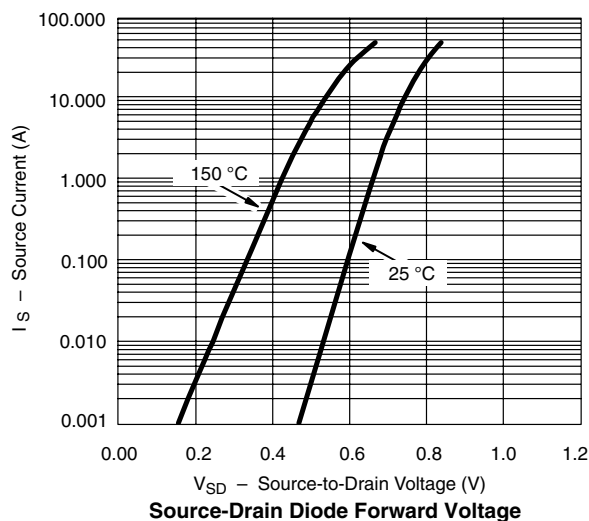
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	25			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		28		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 6		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		2.2	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 16 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 25 V, V _{GS} = 0 V			1	μA
		V _{DS} = 25 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0022	0.0027	Ω
		V _{GS} = 4.5 V, I _D = 15 A		0.0026	0.0032	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 20 A		120		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		6670		pF
Output Capacitance	C _{oss}			997		
Reverse Transfer Capacitance	C _{rss}			531		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A		107.5	161	nC
		V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 20 A		49	73	
Gate-Source Charge	Q _{gs}			15.7		
Gate-Drain Charge	Q _{gd}			13.6		
Gate Resistance	R _g	f = 1 MHz		1.5	2.25	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω		37	56	ns
Rise Time	t _r			122	185	
Turn-Off DelayTime	t _{d(off)}			47	71	
Fall Time	t _f			15	23	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		17	26	
Rise Time	t _r			93	140	
Turn-Off DelayTime	t _{d(off)}			60	90	
Fall Time	t _f			9	15	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			7	A
Pulse Diode Forward Current ^a	I _{SM}				70	
Body Diode Voltage	V _{SD}	I _S = 3 A		0.72	1.1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 13 A, di/dt = 100 A/μs, T _J = 25 °C		47	70	ns
Body Diode Reverse Recovery Charge	Q _{rr}			50	75	nC
Reverse Recovery Fall Time	t _a			23		ns
Reverse Recovery Rise Time	t _b			24		

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

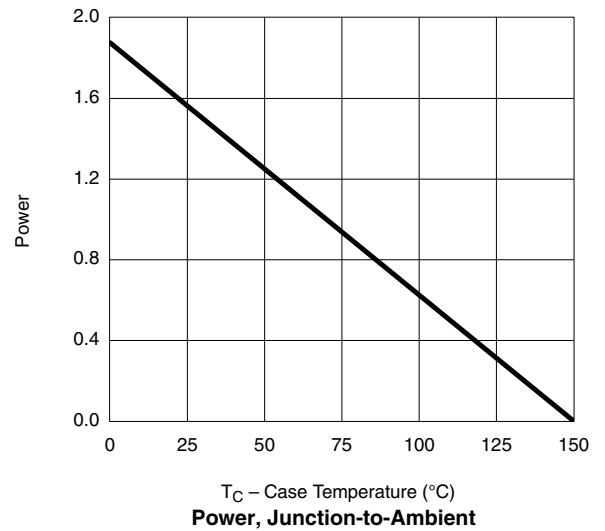
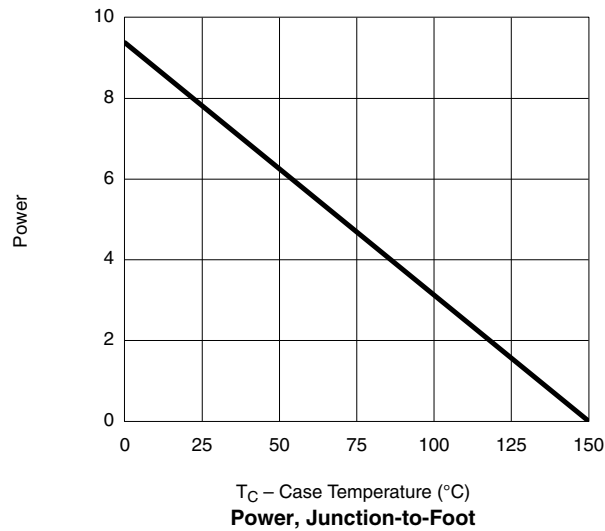
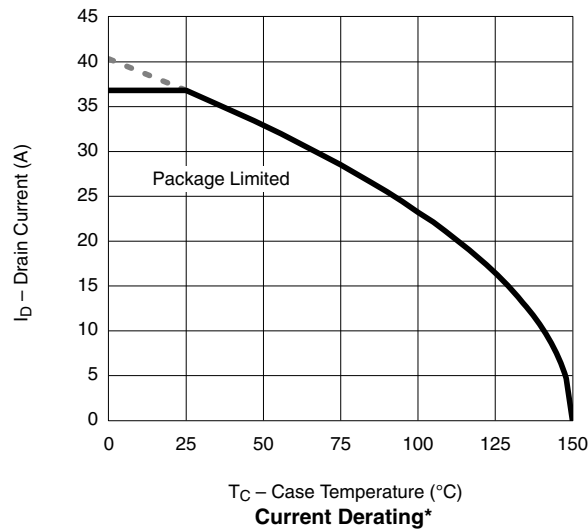
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

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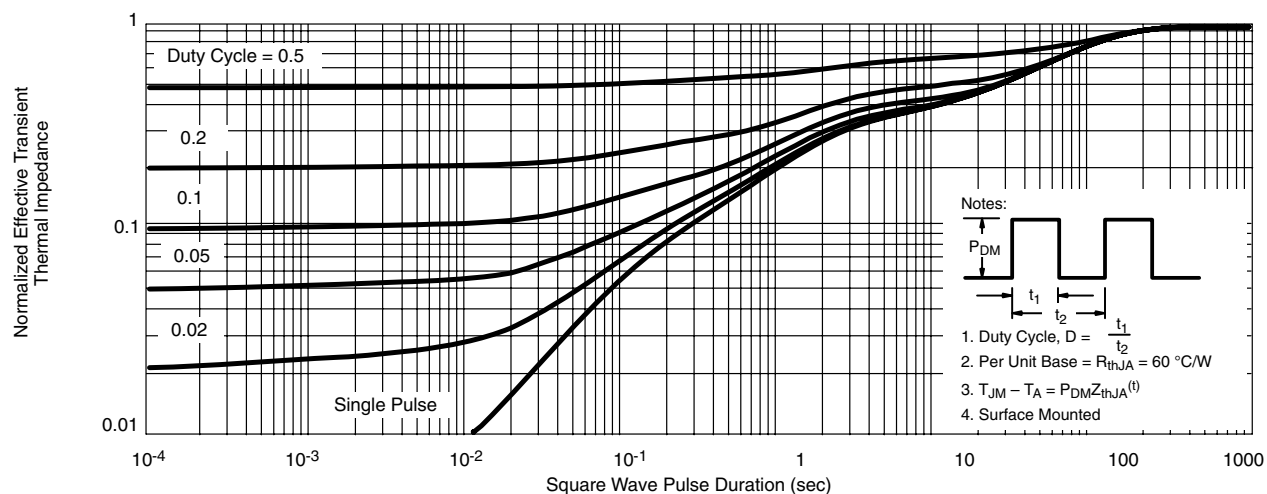
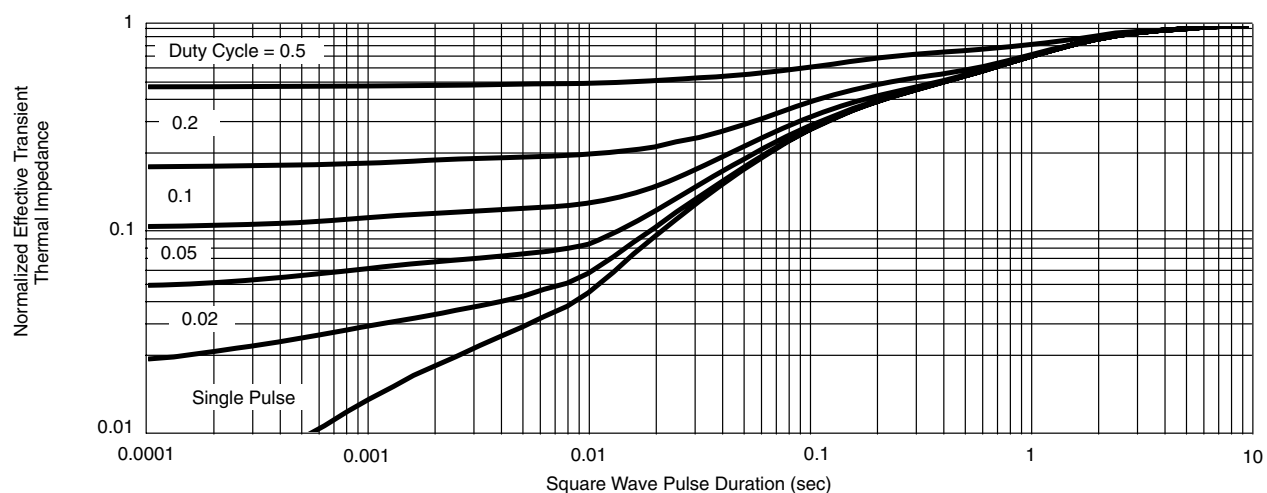
* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

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